

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A method of forming quantum dots, the method comprising:

~~an forming an~~ $\text{In}_x\text{Ga}_{1-x}\text{As}$ strained layer ~~formed on~~ a buffer layer; and

~~forming the~~ $\text{In}(\text{Ga})\text{As}$ quantum dots ~~formed on~~ the $\text{In}_x\text{Ga}_{1-x}\text{As}$ strained layer.
2. (Original) The method of forming quantum dots of claim 1, wherein the buffer layer is made of InAlAs , InAlGaAs , InP , InGaAsP or is a heterojunction layer of at least two of these four materials.
3. (Original) The method of forming quantum dots of claim 1, wherein in the $\text{In}_x\text{Ga}_{1-x}\text{As}$ strained layer, "x" is 0.05 ~ 0.45.
4. (Original) The method of forming quantum dots of claim 1, wherein the thickness of the $\text{In}_x\text{Ga}_{1-x}\text{As}$ strained layer is in a range of 0.5 nm ~ 10 nm.
5. (Original) The method of forming quantum dots of claim 1, wherein $\text{In}(\text{Ga})\text{As}$ quantum dots are formed by metal organic chemical vapor deposition (MOCVD), molecular beam epitaxial (MBE), or chemical beam epitaxial (CBE).
6. (Currently Amended) The method of forming quantum dots of claim 1, wherein the thickness of the ~~$\text{In}_x\text{Ga}_{1-x}\text{As}$~~ $\text{In}(\text{Ga})\text{As}$ quantum dots is 3 ~ 10 monolayers.

7. (Currently Amended) The method of forming quantum dots of claim 1, wherein the $\text{In}_x\text{Ga}_{1-x}\text{As}$ strained layer 5 and the $\text{In}(\text{Ga})\text{As}$ quantum dots 7 can be stacked 1 to 30 sets on top of one another.

8. (New) A method of forming quantum dots, the method comprising:
forming a lattice-matched buffer layer on an InP substrate;
forming an $\text{In}_x\text{Ga}_{1-x}\text{As}$ strained layer on the lattice-matched buffer layer; and
forming the $\text{In}(\text{Ga})\text{As}$ quantum dots on the $\text{In}_x\text{Ga}_{1-x}\text{As}$ strained layer;
wherein the $\text{In}_x\text{Ga}_{1-x}\text{As}$ strained layer changes the surface structure of the lattice-matched buffer layer and alters a strain energy that is necessary to grow the $\text{In}(\text{Ga})\text{As}$ quantum dots.

9. (New) The method of forming quantum dots of claim 8, wherein the buffer layer is made of InAlAs , InAlGaAs , InP , InGaAsP or is a heterojunction layer of at least two of these four materials.

10. (New) The method of forming quantum dots of claim 8, wherein in the $\text{In}_x\text{Ga}_{1-x}\text{As}$ strained layer, x is in a range of 0.05 to 0.45.

11. (New) The method of forming quantum dots of claim 8, wherein the thickness of the $\text{In}_x\text{Ga}_{1-x}\text{As}$ strained layer is in a range of 0.5 nm to 10 nm.